

# Yuzo Shigesato

## List of Publications by Year in descending order

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166  
papers

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172  
docs citations

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times ranked

4279  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical and structural properties of low resistivity tin-doped indium oxide films. Journal of Applied Physics, 1992, 71, 3356-3364.	2.5	352
2	A microstructural study of low resistivity tin-doped indium oxide prepared by d.c. magnetron sputtering. Thin Solid Films, 1994, 238, 44-50.	1.8	201
3	Study of the effect of Sn doping on the electronic transport properties of thin film indium oxide. Applied Physics Letters, 1993, 62, 1268-1270.	3.3	185
4	Thin film TiO <sub>2</sub> photocatalyst deposited by reactive magnetron sputtering. Thin Solid Films, 2003, 442, 227-231.	1.8	185
5	Origin of characteristic grain-subgrain structure of tin-doped indium oxide films. Thin Solid Films, 1995, 259, 38-45.	1.8	131
6	Transparent conductive Nb-doped TiO <sub>2</sub> films deposited by direct-current magnetron sputtering using a TiO <sub>2</sub> target. Thin Solid Films, 2008, 516, 5758-5762.	1.8	130
7	Study of the effect of ion implantation on the electrical and microstructural properties of tin-doped indium oxide thin films. Journal of Applied Physics, 1993, 73, 3805-3811.	2.5	117
8	Electrical and Structural Properties of Tin-Doped Indium Oxide Films Deposited by DC Sputtering at Room Temperature. Japanese Journal of Applied Physics, 1999, 38, 2921-2927.	1.5	115
9	Thermal transport properties of polycrystalline tin-doped indium oxide films. Journal of Applied Physics, 2009, 105, .	2.5	103
10	Crystallinity and electrical properties of tin-doped indium oxide films deposited by DC magnetron sputtering. Applied Surface Science, 1991, 48-49, 269-275.	6.1	101
11	Study on Crystallinity of Tin-Doped Indium Oxide Films Deposited by DC Magnetron Sputtering. Japanese Journal of Applied Physics, 1998, 37, 1870-1876.	1.5	100
12	Photochromic Properties of Amorphous WO <sub>3</sub> Films. Japanese Journal of Applied Physics, 1991, 30, 1457-1462.	1.5	86
13	Doping mechanisms of tin-doped indium oxide films. Applied Physics Letters, 1992, 61, 73-75.	3.3	83
14	Electrical properties of heteroepitaxial grown tin-doped indium oxide films. Journal of Applied Physics, 1996, 80, 978-984.	2.5	83
15	Experimental observation on the Fermi level shift in polycrystalline Al-doped ZnO films. Journal of Applied Physics, 2012, 112, .	2.5	83
16	Preparation and Crystallization of Tin-doped and Undoped Amorphous Indium Oxide Films Deposited by Sputtering. Japanese Journal of Applied Physics, 1999, 38, 5224-5226.	1.5	81
17	Analysis on thermal properties of tin doped indium oxide films by picosecond thermoreflectance measurement. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1180-1186.	2.1	79
18	Heteroepitaxial growth of tin-doped indium oxide films on single crystalline yttria stabilized zirconia substrates. Applied Physics Letters, 1994, 64, 2712-2714.	3.3	75

#	ARTICLE	IF	CITATIONS
19	Thermochromic VO <sub>2</sub> Films Deposited by RF Magnetron Sputtering Using V <sub>2</sub> O <sub>3</sub> or V <sub>2</sub> O <sub>5</sub> Targets. Japanese Journal of Applied Physics, 2000, 39, 6016-6024.	1.5	75
20	Emission spectroscopy during direct-current-biased, microwave-plasma chemical vapor deposition of diamond. Applied Physics Letters, 1993, 63, 314-316.	3.3	73
21	Study on Electronic Structure and Optoelectronic Properties of Indium Oxide by First-Principles Calculations. Japanese Journal of Applied Physics, 1997, 36, 5551-5554.	1.5	72
22	The Structural Changes of Indium-Tin Oxide and α-WO <sub>3</sub> Films by Introducing Water to the Deposition Processes. Japanese Journal of Applied Physics, 1991, 30, 814-819.	1.5	70
23	Study on Thermochromic VO <sub>2</sub> Films Grown on ZnO-Coated Glass Substrates for "Smart Windows". Japanese Journal of Applied Physics, 2003, 42, 6523-6531.	1.5	68
24	Electronic Structure Analyses of Sn-doped In <sub>2</sub> O <sub>3</sub> . Japanese Journal of Applied Physics, 2001, 40, 3231-3235.	1.5	67
25	Temperature dependence of thermal conductivity of VO <sub>2</sub> thin films across metal-insulator transition. Japanese Journal of Applied Physics, 2015, 54, 053201.	1.5	65
26	A time-resolved reflectivity study of the amorphous-to-crystalline transformation kinetics in dc-magnetron sputtered indium tin oxide. Journal of Applied Physics, 1998, 83, 145-154.	2.5	62
27	Doping Mechanisms of Sn in In <sub>2</sub> O <sub>3</sub> Powder Studied Using <sup>119</sup> Sn Mössbauer Spectroscopy and X-Ray Diffraction. Japanese Journal of Applied Physics, 1999, 38, 2856-2862.	1.5	59
28	Thermal Conductivity of Amorphous Indium-Gallium-Zinc Oxide Thin Films. Applied Physics Express, 2013, 6, 021101.	2.4	59
29	Al-Doped ZnO Films Deposited by Reactive Magnetron Sputtering in Mid-Frequency Mode with Dual Cathodes. Japanese Journal of Applied Physics, 2002, 41, 814-819.	1.5	55
30	Oriented Tin-Doped Indium Oxide Films on (100) Preferred Oriented Polycrystalline ZnO Films. Japanese Journal of Applied Physics, 1995, 34, 1638-1642.	1.5	53
31	Microstructure of Low-Resistivity Tin-Doped Indium Oxide Films Deposited at 150 °C. Japanese Journal of Applied Physics, 1995, 34, L244-L247.	1.5	51
32	Structural, electrical, and optical properties of transparent conductive In <sub>2</sub> O <sub>3</sub> -SnO <sub>2</sub> films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1167-1172.	2.1	51
33	Nanocrystalline germanium synthesis from hydrothermally oxidized Si <sub>1-x</sub> Ge <sub>x</sub> alloys. Applied Physics Letters, 1992, 60, 2886-2888.	3.3	50
34	Donor Compensation and Carrier-Transport Mechanisms in Tin-doped In <sub>2</sub> O <sub>3</sub> Films Studied by Means of Conversion Electron <sup>119</sup> Sn Mössbauer Spectroscopy and Hall Effect Measurements. Japanese Journal of Applied Physics, 2000, 39, 4158-4163.	1.5	48
35	Assembled structures of nanocrystals in polymer/calcium carbonate thin-film composites formed by the cooperation of chitosan and poly(aspartate). Journal of Polymer Science Part A, 2006, 44, 5153-5160.	2.3	48
36	DC sputter deposition of amorphous indium-gallium-zinc oxide (a-IGZO) films with H <sub>2</sub> O introduction. Thin Solid Films, 2010, 518, 3004-3007.	1.8	46

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37	Crystallinity of Gallium-Doped Zinc Oxide Films Deposited by DC Magnetron Sputtering Using Ar, Ne or Kr Gas. Japanese Journal of Applied Physics, 2002, 41, 6174-6179.	1.5	45
38	Impedance Control of Reactive Sputtering Process in Mid-Frequency Mode with Dual Cathodes to Deposit Al-Doped ZnO Films. Japanese Journal of Applied Physics, 2003, 42, 263-269.	1.5	44
39	Study on inverse spinel zinc stannate, Zn <sub>2</sub> SnO <sub>4</sub> , as transparent conductive films deposited by rf magnetron sputtering. Thin Solid Films, 2009, 518, 1304-1308.	1.8	44
40	Effects of Energetic Ion Bombardment on Structural and Electrical Properties of Al-Doped ZnO Films Deposited by RF-Superimposed DC Magnetron Sputtering. Japanese Journal of Applied Physics, 2010, 49, 071103.	1.5	44
41	Thermophysical properties of aluminum oxide and molybdenum layered films. Thin Solid Films, 2010, 518, 3119-3121.	1.8	42
42	Crystallinity and Photocatalytic Activity of TiO <sub>2</sub> Films Deposited by Reactive Sputtering Using Various Magnetic Field Strengths. Japanese Journal of Applied Physics, 2004, 43, L442-L445.	1.5	41
43	Bias-enhanced nucleation of diamond during microwave-assisted chemical vapor deposition. Journal of Applied Physics, 1994, 75, 5001-5008.	2.5	40
44	Comparative study on early stages of film growth for transparent conductive oxide films deposited by dc magnetron sputtering. Thin Solid Films, 2008, 516, 4598-4602.	1.8	40
45	Influence of dopant species and concentration on grain boundary scattering in degenerately doped In <sub>2</sub> O <sub>3</sub> thin films. Thin Solid Films, 2016, 614, 62-68.	1.8	40
46	Carrier Density Dependence of Optical Band Gap and Work Function in Sn-Doped In <sub>2</sub> O <sub>3</sub> Films. Applied Physics Express, 2010, 3, 061101.	2.4	38
47	Electrical and optical properties of Nb-doped TiO <sub>2</sub> films deposited by dc magnetron sputtering using slightly reduced Nb-doped TiO <sub>2-x</sub> ceramic targets. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 851-855.	2.1	36
48	Crystal Structure and Photocatalytic Activity of TiO <sub>2</sub> Films Deposited by Reactive Sputtering Using Ne, Ar, Kr, or Xe Gases. Japanese Journal of Applied Physics, 2004, 43, L358-L361.	1.5	35
49	<i>In situ</i> analyses on negative ions in the sputtering process to deposit Al-doped ZnO films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 846-850.	2.1	34
50	Al-doped ZnO (AZO) films deposited by reactive sputtering with unipolar-pulsing and plasma-emission control systems. Thin Solid Films, 2010, 518, 2980-2983.	1.8	33
51	Interfacial stability of an indium tin oxide thin film deposited on Si and Si <sub>0.85</sub> Ge <sub>0.15</sub> . Journal of Applied Physics, 2000, 88, 3717-3724.	2.5	32
52	Photocatalytic Properties of TiO <sub>2</sub> Films Deposited by Reactive Sputtering in Mid-Frequency Mode with Dual Cathodes. Japanese Journal of Applied Physics, 2004, 43, 8234-8241.	1.5	32
53	<i>In situ</i> analyses on negative ions in the indium-gallium-zinc oxide sputtering process. Applied Physics Letters, 2013, 103, .	3.3	31
54	Thermal conductivity of hetero-epitaxial ZnO thin films on c- and r-plane sapphire substrates: Thickness and grain size effect. Journal of Applied Physics, 2019, 125, .	2.5	31

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55	Lattice Defects in O+Implanted Tin-Doped Indium Oxide Films. Japanese Journal of Applied Physics, 1993, 32, L1352-L1355.	1.5	30
56	In Situ Observation of Adsorbed Heptylviologen Cation Radicals by Slab Optical Waveguide Spectroscopy Utilizing Indium-tin-oxide Electrode. Chemistry Letters, 1998, 27, 125-126.	1.3	30
57	Structure and Internal Stress of Tin-Doped Indium Oxide and Indium-Zinc Oxide Films Deposited by DC Magnetron Sputtering. Japanese Journal of Applied Physics, 2007, 46, 7806-7811.	1.5	30
58	On the Crystal Structural Control of Sputtered TiO <sub>2</sub> Thin Films. Nanoscale Research Letters, 2016, 11, 324.	5.7	30
59	Electrochromic Properties of Li <sub>x</sub> Ni <sub>y</sub> O Films Deposited by RF Magnetron Sputtering. Journal of the Electrochemical Society, 2009, 156, H629.	2.9	29
60	Sputter deposition of Al-doped ZnO films with various incident angles. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1166-1171.	2.1	28
61	Origin of carrier scattering in polycrystalline Al-doped ZnO films. Applied Physics Express, 2014, 7, 105802.	2.4	28
62	Effects of Magnetic Field Gradient on Crystallographic Properties in Tin-Doped Indium Oxide Films Deposited by Electron Cyclotron Resonance Plasma Sputtering. Japanese Journal of Applied Physics, 1994, 33, 4997-5004.	1.5	27
63	Effects of water partial pressure on the activated electron beam evaporation process to deposit tin-doped indium oxide films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 268-275.	2.1	27
64	Effects of Tin Concentrations on Structural Characteristics and Electrooptical Properties of Tin-Doped Indium Oxide Films Prepared by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 1995, 34, 600-605.	1.5	27
65	Study on Fluorine-Doped Indium Oxide Films Deposited by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2000, 39, 6422-6426.	1.5	27
66	Electrical and optical properties of Al-doped ZnO films deposited by hollow cathode gas flow sputtering. Thin Solid Films, 2009, 517, 3048-3052.	1.8	27
67	Thermophysical and electrical properties of Al-doped ZnO films. Journal of Applied Physics, 2012, 111, .	2.5	27
68	Comparative study of heteroepitaxial and polycrystalline tin-doped indium oxide films. Journal of Non-Crystalline Solids, 1997, 218, 267-272.	3.1	25
69	Evolution of Defect Structures and Deep Subgap States during Annealing of Amorphous In-Ga-Zn Oxide for Thin-Film Transistors. Physical Review Applied, 2018, 9, .	3.8	25
70	Nucleation and growth during the chemical vapor deposition of diamond on SiO <sub>2</sub> substrates. Journal of Materials Research, 1994, 9, 2164-2173.	2.6	24
71	Electronic State of Amorphous Indium Gallium Zinc Oxide Films Deposited by DC Magnetron Sputtering with Water Vapor Introduction. Applied Physics Express, 2012, 5, 075802.	2.4	24
72	Transparent conductive Nb-doped TiO <sub>2</sub> films deposited by reactive dc sputtering using Ti-Nb alloy target, precisely controlled in the transition region using impedance feedback system. Applied Surface Science, 2014, 301, 551-556.	6.1	24

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73	Study on early stages of film growth for Sn doped In <sub>2</sub> O <sub>3</sub> films deposited at various substrate temperatures. Thin Solid Films, 2008, 516, 5868-5871.	1.8	23
74	Study on MoO <sub>3</sub> films deposited by reactive sputtering for organic light-emitting diodes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 886-889.	2.1	23
75	Amorphous indium-tin-zinc oxide films deposited by magnetron sputtering with various reactive gases: Spatial distribution of thin film transistor performance. Applied Physics Letters, 2015, 106, .	3.3	23
76	Visible-light active thin-film WO <sub>3</sub> photocatalyst with controlled high-rate deposition by low-damage reactive-gas-flow sputtering. APL Materials, 2015, 3, 104407.	5.1	23
77	A visible-light active TiO <sub>2</sub> photocatalyst multilayered with WO <sub>3</sub> . Physical Chemistry Chemical Physics, 2017, 19, 17342-17348.	2.8	23
78	Photoinduced Hydrophilicity of Epitaxially Grown TiO <sub>2</sub> Films by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2003, 42, L1529-L1531.	1.5	22
79	Al-doped ZnO films deposited on a slightly reduced buffer layer by reactive dc unbalanced magnetron sputtering. Thin Solid Films, 2014, 555, 93-99.	1.8	22
80	High-rate deposition of Sb-doped SnO <sub>2</sub> films by reactive sputtering using the impedance control method. Thin Solid Films, 2011, 520, 1178-1181.	1.8	21
81	Transparent conductive Al and Ga doped ZnO films deposited using off-axis sputtering. Thin Solid Films, 2014, 559, 69-77.	1.8	21
82	Crystallization behavior of amorphous indium-gallium-zinc-oxide films and its effects on thin-film transistor performance. Japanese Journal of Applied Physics, 2016, 55, 035504.	1.5	21
83	Visible-Light Active Photocatalytic WO <sub>3</sub> Films Loaded with Pt Nanoparticles Deposited by Sputtering. Journal of Nanoscience and Nanotechnology, 2012, 12, 5082-5086.	0.9	20
84	Direct observation of the band gap shrinkage in amorphous In <sub>2</sub> O <sub>3</sub> -ZnO thin films. Journal of Applied Physics, 2013, 113, .	2.5	20
85	Electron microscopic and ion scattering studies of heteroepitaxial tin-doped indium oxide films. Applied Physics Letters, 1994, 65, 546-548.	3.3	19
86	Visible light-induced photocatalytic properties of WO <sub>3</sub> films deposited by dc reactive magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	2.1	19
87	Thermophysical Properties of Transparent Conductive Nb-Doped TiO <sub>2</sub> Films. Japanese Journal of Applied Physics, 2012, 51, 035802.	1.5	19
88	Structure Analysis of ZnO-TeO <sub>2</sub> Glasses by Means of Neutron Diffraction and Molecular Dynamics. Japanese Journal of Applied Physics, 1996, 35, 694-698.	1.5	18
89	High-rate deposition of high-quality Sn-doped In <sub>2</sub> O <sub>3</sub> films by reactive magnetron sputtering using alloy targets. Thin Solid Films, 2012, 520, 4101-4105.	1.8	18
90	Comparative study of sputtered-deposited SnO <sub>2</sub> films doped with antimony or tantalum. Physica Status Solidi (B): Basic Research, 2016, 253, 923-928.	1.5	18

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91	ITO thin-film transparent conductors: Microstructure and processing. <i>Jom</i> , 1995, 47, 47-50.	1.9	17
92	High rate reactive magnetron sputter deposition of Al-doped ZnO with unipolar pulsing and impedance control system. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2010, 28, 890-894.	2.1	17
93	Spatial distribution of electrical properties for Al-doped ZnO films deposited by dc magnetron sputtering using various inert gases. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2010, 28, 895-900.	2.1	16
94	In-situ analyses on the reactive sputtering process to deposit Al-doped ZnO films using an Al-Zn alloy target. <i>Thin Solid Films</i> , 2012, 520, 3751-3754.	1.8	16
95	Thermal Boundary Resistance of W/Al <sub>2</sub> O <sub>3</sub> Interface in W/Al <sub>2</sub> O <sub>3</sub> /W Three-Layered Thin Film and Its Dependence on Morphology. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 065802.	1.5	15
96	Diamond nucleation on unscratched SiO <sub>2</sub> substrates. <i>Applied Physics Letters</i> , 1994, 65, 210-212.	3.3	14
97	Thermal Diffusivities of Tris(8-hydroxyquinoline)aluminum and N,N'-Di(1-naphthyl)-N,N'-diphenylbenzidine Thin Films with Sub-Hundred Nanometer Thicknesses. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 121602.	1.5	14
98	Effect of nitrogen addition on the structural, electrical, and optical properties of In-Sn-Zn oxide thin films. <i>Applied Surface Science</i> , 2017, 396, 897-901.	6.1	14
99	Effect of Sn Doping on the Crystal Growth of Indium Oxide Films. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 6585-6586.	1.5	13
100	Novel emission properties of melem caused by the heavy metal effect of lanthanides(iii) in a LB film. <i>Photochemical and Photobiological Sciences</i> , 2007, 6, 804.	2.9	13
101	High rate deposition of photocatalytic TiO <sub>2</sub> films with high activity by hollow cathode gas-flow sputtering method. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008, 26, 893-897.	2.1	13
102	Thermophysical properties of SnO <sub>2</sub> -based transparent conductive films: Effect of dopant species and structure compared with In <sub>2</sub> O <sub>3</sub> -, ZnO-, and TiO <sub>2</sub> -based films. <i>Journal of Materials Research</i> , 2014, 29, 1579-1584.	2.6	13
103	Characterization of RF-Enhanced DC Sputtering to Deposit Tin-Doped Indium Oxide Thin Films. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 6210-6214.	1.5	12
104	Electrical properties and surface morphology of heteroepitaxial-grown tin-doped indium oxide thin films deposited by molecular-beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2000, 18, 1663-1667.	2.1	12
105	Excitation energy transfer between D3h melamines and Pr(III) in the solid state. <i>Science and Technology of Advanced Materials</i> , 2006, 7, 72-76.	6.1	12
106	High rate deposition of photocatalytic TiO <sub>2</sub> films by dc magnetron sputtering using a TiO <sub>2-x</sub> target. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008, 26, 903-907.	2.1	12
107	Tailoring the crystal structure of TiO <sub>2</sub> thin films from the anatase to rutile phase. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	2.1	12
108	p-type conduction mechanism in continuously varied non-stoichiometric SnO <sub>x</sub> thin films deposited by reactive sputtering with the impedance control. <i>Journal of Applied Physics</i> , 2020, 127, 185703.	2.5	12

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109	Molecular Distortion Effect on ff-Emission in a Pr(III) Complex with 4,7-Diphenyl-1,10-Phenanthroline. <i>ChemPhysChem</i> , 2007, 8, 1345-1351.	2.1	11
110	In-situ Analyses on Reactive Sputtering Processes to Deposit Photocatalytic TiO <sub>2</sub> Films. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 041105.	1.5	11
111	Structure and thermophysical properties of GaN films deposited by reactive sputtering using a metal Ga target. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, .	2.1	11
112	GaN Films Deposited by DC Reactive Magnetron Sputtering. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L164-L166.	1.5	10
113	Donor generation from native defects induced by In <sup>+</sup> implantation into tin-doped indium oxide. <i>Journal of Applied Physics</i> , 1995, 77, 2572-2575.	2.5	9
114	In-situ analysis of positive and negative energetic ions generated during Sn-doped In <sub>2</sub> O <sub>3</sub> deposition by reactive sputtering. <i>Thin Solid Films</i> , 2011, 520, 1182-1185.	1.8	9
115	Photocatalytic Activity of WO <sub>3</sub> Films Crystallized by Postannealing in Air. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 055501.	1.5	9
116	Photocatalytic oxidation of benzene in a microreactor with immobilized TiO <sub>2</sub> thin films deposited by sputtering. <i>Catalysis Communications</i> , 2017, 100, 1-4.	3.3	9
117	Temporal Evolution of Microscopic Structure and Functionality during Crystallization of Amorphous Indium-Based Oxide Films. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 31825-31834.	8.0	9
118	Study on reactive sputtering to deposit transparent conductive amorphous In <sub>2</sub> O <sub>3</sub> -ZnO films using an In-Zn alloy target. <i>Thin Solid Films</i> , 2014, 559, 49-52.	1.8	8
119	Oxidation Resistance of Ti-Si-N and Ti-Al-Si-N Films Deposited by Reactive Sputtering Using Alloy Targets. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 075802.	1.5	8
120	Effect of Oxygen Impurities on Thermal Diffusivity of AlN Thin Films Deposited by Reactive RF Magnetron Sputtering. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 11RB01.	1.5	7
121	Nanocrystalline Ge synthesis by the chemical reduction of hydrothermally grown Si <sub>0.6</sub> Ge <sub>0.4</sub> O <sub>2</sub> . <i>Journal of Electronic Materials</i> , 1994, 23, 901-906.	2.2	6
122	Influence of Unbalanced Magnetron and Penning Ionization for RF Reactive Magnetron Sputtering. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 186-191.	1.5	6
123	High-Performance and High-CRI OLEDs for Lighting and Their Fabrication Processes. <i>Advances in Science and Technology</i> , 2010, 75, 65-73.	0.2	6
124	Comparison of CF <sub>4</sub> and C <sub>4</sub> F <sub>8</sub> gas etching profiles by multiscale simulation. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 036501.	1.5	6
125	Tuning hole charge collection efficiency in polymer photovoltaics by optimizing the work function of indium tin oxide electrodes with solution-processed LiF nanoparticles. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 9205-9212.	2.2	6
126	Indium oxide-based transparent conductive films deposited by reactive sputtering using alloy targets. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 045503.	1.5	6



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127	Carrier densities of Sn-doped In <sub>2</sub> O <sub>3</sub> nanoparticles and their effect on X-ray photoelectron emission. Journal of Applied Physics, 2019, 125, 245303.	2.5	6
128	Effect of Oxygen Impurities on Thermal Diffusivity of AlN Thin Films Deposited by Reactive RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2011, 50, 11RB01.	1.5	5
129	Crystallization behavior during transparent In <sub>2</sub> O <sub>3</sub> /ZnO film growth. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2291-2295.	1.8	5
130	Thermophysical Properties of Transparent Conductive Nb-Doped TiO <sub>2</sub> Films. Japanese Journal of Applied Physics, 2012, 51, 035802.	1.5	5
131	Microstructure of Heteroepitaxially Grown TiO <sub>2</sub> Films by Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2001, 672, 1.	0.1	4
132	Formation of homologous In <sub>2</sub> O <sub>3</sub> (ZnO) <sub>m</sub> thin films and its thermoelectric properties. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 041507.	2.1	4
133	Geometric structure of Sn dopants in sputtered TiO <sub>2</sub> film revealed by x-ray absorption spectroscopy and first-principles DFT calculations. Materials Research Express, 2018, 5, 046412.	1.6	4
134	Thermal conductivity across the van der Waals layers of In <sub>2</sub> S <sub>3</sub> -MoO <sub>3</sub> thin films composed of mosaic domains with in-plane 90° rotations. Journal of Applied Physics, 2021, 130, .	2.5	4
135	High Rate Reactive Sputter Deposition of TiO <sub>2</sub> Films for Photocatalyst and Dye-Sensitized Solar Cells. Japanese Journal of Applied Physics, 2011, 50, 045802.	1.5	4
136	Photocatalytic Activity of WO <sub>3</sub> Films Crystallized by Postannealing in Air. Japanese Journal of Applied Physics, 2012, 51, 055501.	1.5	4
137	Structures and Electrical Properties of Tin Doped Indium Oxide (ITO) Films Deposited on Different Substrates by Sputtering with H <sub>2</sub> O Introduction. Shinku/Journal of the Vacuum Society of Japan, 2004, 47, 796-801.	0.2	3
138	How the sputtering process influence structural, optical, and electrical properties of Zn <sub>3</sub> N <sub>2</sub> films?. MRS Communications, 2018, 8, 314-321.	1.8	3
139	Metallization in a-Si:H TFT Array Fabrication by Deposition and Wet Etching of Conductors. , 2004, , 313-376.		3
140	Thermal Boundary Resistance between Ni-Bis(1-naphthyl)-N-diphenylbenzidine and Aluminum Films. Japanese Journal of Applied Physics, 2011, 50, 11RB02.	1.5	3
141	Nanocrystalline Ge Synthesis by Reduction of Si <sub>1-x</sub> Ge <sub>x</sub> O <sub>2</sub> Formed by High Pressure Oxidation. Materials Research Society Symposia Proceedings, 1992, 283, 51.	0.1	2
142	Thermochromic nondoped and W-doped VO <sub>2</sub> films heteroepitaxially grown on glass substrate using ZnO polycrystalline films as buffer layers. , 2001, , .		2
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